04-07-03

AF/2800

Attorney Docket No. FUJ 99228 CIP
Client Matter. No. 80458.0011

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Katsuyoshi MATSUURA, et al.

Serial No. 09/551,233

Filed: April 17, 2000

Title: SEMICONDUCTOR DEVICE HAVING A FERROELECTRIC CAPACITOR AND A FABRICATION PROCESS THEREOF

Examiner: H.-M. LEE

Art Unit: 2823

CERTIFICATE OF MAILING BY EXPRESS MAIL

BOX: AF
Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

The undersigned hereby certifies that the attached

1. Amendment & Response to Final Office Action;
2. Return Card, and

this Certificate of Mailing by Express Mail relating to the above application, were deposited as "Express Mail," Mailing Label No. EL533455286US with the U.S. Postal Service, addressed to Attention: Box: AF, Assistant Commissioner for Patents, Washington, D.C. 20231, on April 2, 2003.

April 2, 2003

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April 2, 2003

Carol W. Burton, Reg. No. 35465
Hogan & Hartson LLP
1200 17th Street, Suite 1500
Denver, Colorado 80202
(303) 454-2454 (telephone)
(303) 899-7333 (facsimile)

#20/E (NE)
4-11-03

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AMENDMENT & RESPONSE TO FINAL OFFICE ACTION

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Final Office Action mailed February 4, 2003 in the above-referenced application, please enter the following amendments and consider the remarks which follow.

IN THE CLAIMS:

Please amend claims 1, 12, 14, 15 and 21 according to the attached sheets.

REMARKS

In the Final Office Action of February 4, 2003, claims 1, 2, 4-12,14-19 and 21-28 were examined and rejected under 35 U.S.C. §103(a) over a combination of U.S. Patents to *Cuchiaro et al., Chu et al.* and *Izuha et al.* This rejection is respectfully traversed in view of the above amendments and the remarks which follow.

The single §103 rejection is based (page 7) on the contention that:

> By choosing the aforementioned oxygen partial pressure range, Chu et al. suggest that the perovskite structure can form with a large amount of O_2 vacancies embedded in the structure, which would provide effective paths for lead cations to migrate in the PZT film, giving rise to a more uniform lead distribution and more homogeneous formation of a perovskite phase.